

### High power PNP epitaxial planar bipolar transistor

#### **Features**

- High breakdown voltage V<sub>CEO</sub> = -100 V
- Complementary to 2STC2510
- Typical f<sub>t</sub> = 20 MHz
- Fully characterized at 125 °C

#### **Application**

■ Audio power amplifier

#### **Description**

The device is a PNP transistor manufactured using new BiT-LA (Bipolar transistor for linear amplifier) technology. The resulting transistor shows good gain linearity behaviour.

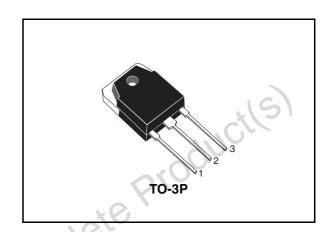


Figure 1. Internal schematic diagram

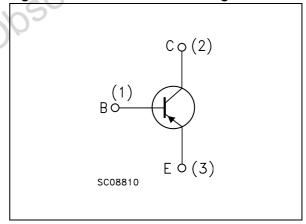


Table 1. Device summary

Order code	Marking	Package	Packaging
2STA2510	2STA2510	TO-3P	Tube

Electrical ratings 2STA2510

# 1 Electrical ratings

Table 2. Absolute maximum rating

Symbol	Parameter	Value	Unit
$V_{CBO}$	Collector-base voltage (I <sub>E</sub> = 0)	-100	V
$V_{CEO}$	Collector-emitter voltage (I <sub>B</sub> = 0)	-100	٧
V <sub>EBO</sub>	Emitter-base voltage ( $I_C = 0$ )	-6	٧
I <sub>C</sub>	Collector current	-25	Α
I <sub>CM</sub>	Collector peak current (t <sub>P</sub> < 5 ms)	-50	А
P <sub>TOT</sub>	Total dissipation at T <sub>c</sub> = 25 °C	125	8
T <sub>stg</sub>	Storage temperature	-65 to 150	°C
TJ	Max. operating junction temperature	150	°C

Table 3. Thermal data

	Symbol	Parameter	16,6	Value	Unit
	R <sub>thj-case</sub>	Thermal resistance junction-case	max	1	°C/W
	··iiij-case	oduci(s)	05		- G/W
Obsol	ete				

## 2 Electrical characteristics

 $(T_{case} = 25 \, ^{\circ}C; \text{ unless otherwise specified})$ 

Table 4. Electrical characteristics

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
I <sub>CBO</sub>	Collector cut-off current (I <sub>E</sub> = 0)	V <sub>CB</sub> = -100 V			-10	μΑ
I <sub>EBO</sub>	Emitter cut-off current (I <sub>C</sub> = 0)	V <sub>EB</sub> = -6 V			-10	μΑ
V <sub>(BR)CEO</sub> <sup>(1)</sup>	Collector-emitter breakdown voltage (I <sub>B</sub> = 0)	I <sub>C</sub> = -50 mA	-100	. 10		>
V <sub>(BR)CBO</sub>	Collector-base breakdown voltage (I <sub>E</sub> = 0)	I <sub>C</sub> = -100 μA	-100	20.		V
V <sub>(BR)EBO</sub> <sup>(1)</sup>	Emitter-base breakdown voltage ( $I_C = 0$ )	I <sub>E</sub> = -1 mA	-6			V
V <sub>CE(sat)</sub> (1)	Collector-emitter saturation voltage	$I_C = -12 \text{ A}$ $I_B = -1.2 \text{ A}$			-1.5	V
V <sub>BE</sub> <sup>(1)</sup>	Base-emitter voltage	$V_{CE} = -4 \text{ V}$ $I_{C} = -12 \text{ A}$			-1.8	V
h <sub>FE</sub>	DC current gain	$I_C = -12 \text{ A}$ $V_{CE} = -4 \text{ V}$	40		80	
f <sub>T</sub>	Transition frequency	$I_C = -0.5 \text{ A}$ $V_{CE} = -12 \text{ V}$		20		MHz

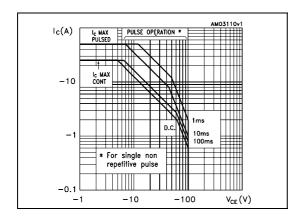
<sup>1.</sup> Pulsed duration = 300 μs, duty cycle ≤ 1.5 %

Electrical characteristics 2STA2510

### 2.1 Electrical characteristic (curves)

Figure 2. Safe operating area

Figure 3. Derating curve



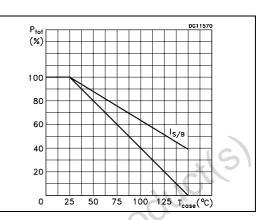
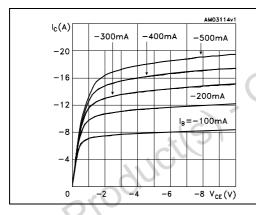


Figure 4. Output characteristics

Figure 5. DC current gain



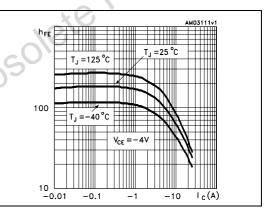
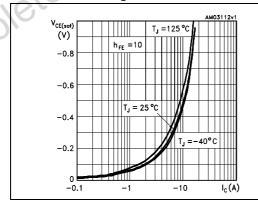
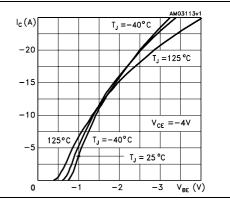


Figure 6. Collector-emitter saturation voltage

Figure 7. Collector current vs baseemitter voltage





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## 3 Package mechanical data

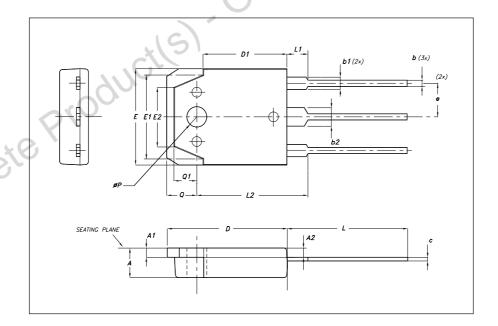
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DIM.		mm.	
DIIVI.	MIN.	TYP	MAX.
A	4.6		5
A1	1.45	1.50	1.65
A2	1.20	1.40	1.60
b	0.80	1	1.20
b1	1.80		2.20
b2	2.80		3.20
С	0.55	0.60	0.75
D	19.70	19.90	20.10
D1		13.90	111
E	15.40		15.80
E1		13.60	100
E2		9.60	7/10
е	5.15	5.45	5.75
L	19.50	20	20.50
L1		3.50	
L2	18.20	18.40	18.60
Р	3.10		3.30
Q		5	
Q1		3.80	



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2STA2510 Revision history

# 4 Revision history

Table 5. Document revision history

Date	Revision	Changes
26-Nov-2007	1	Initial release
16-May-2008	2	Document status promoted from preliminary data to datasheet.
14-Nov-2008	3	Added paragraph: Electrical characteristic (curves) on page 4.

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